

*F1 Sub G*

exposing said conductive material to a material selected from the group consisting of phosphine, and methylsilane.

*Sub G*

76. (Thrice Amended) A method of passivating a conductive layer,

comprising:

*F2*

providing a tungsten nitride layer;

providing a polysilicon layer on the tungsten nitride layer; and

exposing the tungsten nitride layer to a material selected from the group consisting of phosphine, and methylsilane.

*Sub G*

77. (Twice Amended) The method in claim 76, wherein exposing the

tungsten nitride layer comprises exposing the tungsten nitride layer to at least one material in the recited group under process conditions comprising:

a flow rate of the material of about 2 sccm to about 400 sccm;

a flow rate of about 50 sccm to about 100 sccm for an inert carrier gas;

a temperature ranging from about 150 to about 600 degrees Celsius;

a pressure ranging from about 50 millitorr to about 760 torr; and

a process time ranging from about 50 to about 500 seconds.

*Sub G*

81. (Thrice Amended) A method of passivating a conductive layer,

comprising:

*F4*

providing a first conductive plug;

providing a first conductive layer on the plug;

exposing the first conductive layer to a material selected from the group consisting of phosphine, and methylsilane; and

after exposing the first conductive layer, forming a second conductive layer on the first conductive layer.

Please add new claims 89-92 as follows:

*Sub G* ~~--89. (New) The method of claim 4 wherein the conductive layer comprises at least one of tungsten nitride, polysilicon, tungsten, copper, and aluminum.~~

*F5* ~~90. (New) The method of claim 4 wherein exposing said conductive material comprises exposing the conductive material to at least one material in the recited group under process conditions comprising:~~

~~a flow rate of the material of about 2 sccm to about 400 sccm;~~  
~~a flow rate of about 50 sccm to about 100 sccm for an inert carrier gas;~~  
~~a temperature ranging from about 150 to about 600 degrees Celsius;~~  
~~a pressure ranging from about 50 millitorr to about 760 torr; and~~  
~~a process time ranging from about 50 to about 500 seconds.~~

~~91. (New) The method of claim 90 wherein the inert carrier gas comprises He or Ar.~~

~~92. (New) The method of claim 77 wherein the inert carrier gas comprises He or Ar.--~~